

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
14 April 2005 (14.04.2005)

PCT

(10) International Publication Number
WO 2005/034227 A1

(51) International Patent Classification⁷: **H01L 21/304**

(21) International Application Number:
PCT/KR2004/002565

(22) International Filing Date: 7 October 2004 (07.10.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
10-2003-0069969 8 October 2003 (08.10.2003) KR
10-2003-0083709 24 November 2003 (24.11.2003) KR
10-2003-0083671 24 November 2003 (24.11.2003) KR
10-2004-0040264 3 June 2004 (03.06.2004) KR
10-2004-0051189 1 July 2004 (01.07.2004) KR

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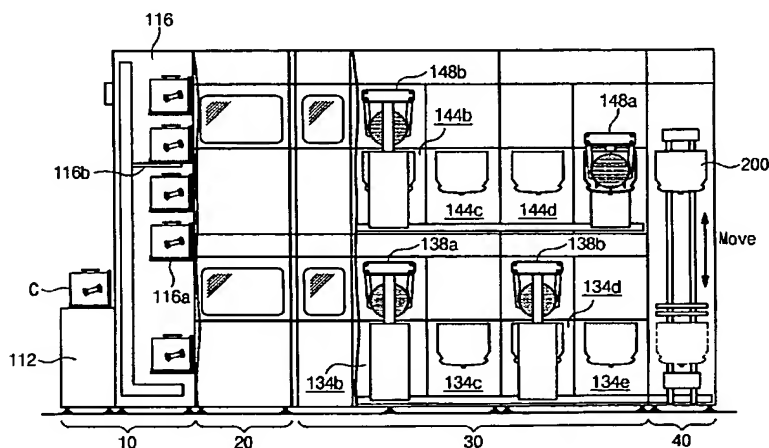
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(81) Designated States (unless otherwise indicated, for every
kind of national protection available): AE, AG, AL, AM,
AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN,
CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI,
GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE,
KG, KP, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG,
MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH,
PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN,
TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every
kind of regional protection available): ARIPO (BW, GH,
GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM,

[Continued on next page]

(54) Title: FACILITY WITH MULTI-STORIED PROCESS CHAMBER FOR CLEANING SUBSTRATES AND METHOD FOR
CLEANING SUBSTRATES USING THE FACILITY



(57) Abstract: A facility for cleaning substrates such as semiconductor wafers includes a loading/unloading part, an aligning part where wafers are repositioned from a horizontal state to a vertical state, a cleaning part performing etchant-treating, rinsing, and drying processes for wafers and having a plurality of process chamber stacked, and an interface part where a transfer bath is disposed to transfer wafers between the process chambers. When the wafers are transferred between the process chambers, the transfer bath is filled with deionized water (DI water) to prevent their exposure to the air. Wafers drawn out of the loading/unloading part are repositioned from a horizontal state to a vertical state and are transferred to a first process chamber being one of the process chambers to be subjected

to a part of processes. After the wafers are transferred to a second process chamber being the other one of the process chambers to be subjected to the other processes, they are repositioned from a vertical state to a horizontal state. That is, the wafers are transferred along a loop shape to be processed.



ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),
European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI,
FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI,
SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ,
GW, ML, MR, NE, SN, TD, TG).

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Published:

— *with international search report*